

NPN wideband silicon germanium RF transistor

Rev. 1 — 8 May 2013

Product data sheet

1. Product profile

1.1 General description

NPN silicon germanium microwave transistor for high speed, low noise applications in a SOT883C leadless ultra small plastic SMD package.

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

1.2 Features and benefits

- Leadless ultra small plastic SMD package 1.0 mm × 0.6 mm × 0.34 mm
- Low noise high gain microwave transistor
- Noise figure (NF) = 0.75 dB at 6 GHz
- High maximum power gain (G_{p(max)}) of 15.8 dB at 6 GHz
- Excellent linearity in WiFi LNA from 5 GHz to 5.9 GHz:
 - input third-order intercept point (IP3_i) = 15 dBm
 - input power at 1 dB gain compression (P_{i(1dB)}) = 0 dBm

See application note AN11224: Low Noise Fast Turn ON/OFF 5-5.9GHz WiFi LNA with BFU730LX.

■ 110 GHz f_T silicon germanium technology

1.3 Applications

Wi-Fi / WLAN

See application notes:

- AN11223: Low Noise Fast Turn ON/OFF 2.4-2.5GHz WiFi LNA with BFU730LX
- AN11224: Low Noise Fast Turn ON/OFF 5-5.9GHz WiFi LNA with BFU730LX
- WiMAX
- LNA for GPS, GLONASS, Galileo and Compass (BeiDou)
- DBS (2nd LNA stage, mixer stage, DRO), SDARS
- RKE, AMR / Zigbee
- LNA for microwave communications systems
- Low current battery equipped applications
- Microwave driver / buffer applications



NPN wideband silicon germanium RF transistor

1.4 Quick reference data

Table 1. Quick reference data

$T_i =$	25	°C	unless	otherwise	specified
---------	----	----	--------	-----------	-----------

Symbol	Parameter	Conditions	Mi	n	Тур	Max	Unit
V _{CB}	collector-base voltage	open emitter	-		-	10.0	V
V_{CE}	collector-emitter voltage	open base	-		-	3.0	V
		shorted base	-		-	10.0	V
V_{EB}	emitter-base voltage	open collector	-		-	1.3	V
I _C	collector current		-		5	30	mA
P _{tot}	total power dissipation	$T_{sp} \le 110 \ ^{\circ}C$	<u>[1]</u> -		-	160	mW
h _{FE}	DC current gain	$ I_C = 2 \text{ mA}; V_{CE} = 2 \text{ V}; $	20	5	380	555	
f _T	transition frequency	$I_C = 25 \text{ mA}; V_{CE} = 3 \text{ V};$ f = 2 GHz; T _{amb} = 25 °C	-		53	-	GHz
G _{p(max)}	maximum power gain	$I_C = 25 \text{ mA}; V_{CE} = 3 \text{ V};$ f = 6 GHz; T _{amb} = 25 °C	[2] _		15.8	-	dB
NF	noise figure	$\label{eq:lc} \begin{array}{l} I_C = 5 \text{ mA}; \ V_{CE} = 3 \text{ V}; \ f = 6 \\ GHz; \ \Gamma_S = \Gamma_{opt} \end{array}$	-		0.75	-	dB
P _{L(1dB)}	output power at 1 dB gain compression	$ \begin{split} & I_{C} = 25 \text{ mA}; V_{CE} = 3 \text{ V}; \\ & Z_{S} = Z_{L} = 50 \ \Omega; \\ & f = 1.8 \text{ GHz}; T_{amb} = 25 \ ^{\circ}C \end{split} $	-		11.7	-	dBm

 $\label{eq:tau} [1] \quad T_{sp} \mbox{ is the temperature at the solder point of the emitter lead}.$

[2] $G_{p(max)}$ is the maximum power gain, if K > 1. If K < 1 then $G_{p(max)}$ = Maximum Stable Gain (MSG).

2. Pinning information

Table 2.	Discrete pinning		
Pin	Description	Simplified outline	Graphic symbol
1	base		2
2	collector		2]
3	emitter	2	1-6
		Transparent top view	ן 3 aaa-006018

3. Ordering information

Table 3.	Ordering information
Tuble 0.	or dering information

Type number	Package				
	Name	Description	Version		
BFU730LX	-	leadless ultra small plastic package; 3 terminals; body 1 \times 0.6 \times 0.34 mm	SOT883C		

Product data sheet

NPN wideband silicon germanium RF transistor

4. Marking

Table 4. Marking	
Type number	Marking
BFU730LX	ZD

5. Design support

Table 5.Available design support

Download from the BFU730LX product page on http://www.nxp.com.

Support item	Available		Remarks
Device models for Agilent EEsof EDA ADS	yes	[1]	Based on Mextram device model
Device models for Agilent EEsof EDA Genesys	yes		Based on Mextram device model
Device models for AWR Microwave Office	planned		Based on Mextram device model
Device models for ANSYS Ansoft designer	planned		Based on Mextram device model
SPICE model	planned		Based on Gummel-Poon device model
S-parameters	yes		
Noise parameters	yes		
Customer evaluation kit	yes		
Gerber files evaluation board	yes		
Reflow soldering footprint	yes		
AN11223: Low Noise Fast Turn ON/OFF 2.4-2.5GHz WiFi LNA with BFU730LX	yes		Application note
AN11224: Low Noise Fast Turn ON/OFF 5-5.9GHz WiFi LNA with BFU730LX	yes		Application note

[1] See <u>http://www.nxp.com/models.html</u>.

6. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CB}	collector-base voltage	open emitter	-	10.0	V
V _{CE}	collector-emitter voltage	open base	-	3.0	V
		shorted base	-	10.0	V
V_{EB}	emitter-base voltage	open collector	-	1.3	V
P _{tot}	total power dissipation	$T_{sp} \le 110 \ ^{\circ}C$	<u>[1]</u>	160	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C

[1] T_{sp} is the temperature at the solder point of the emitter lead.

BFU730LX Product data sheet

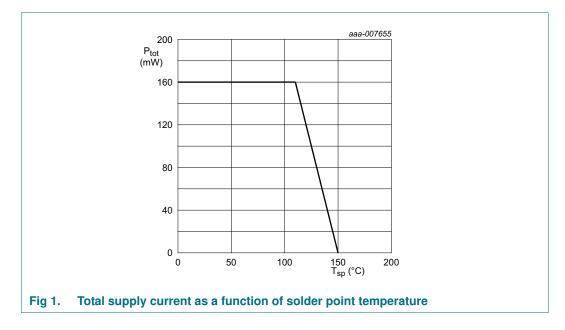
NPN wideband silicon germanium RF transistor

7. Recommended operating conditions

Table 7.	Recommended operation	ng conditions				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Тj	junction temperature		-40	-	+125	°C
I _C	collector current		-	-	30	mA

8. Thermal characteristics

Table	e 8.	Thermal characteristics			
Sym	bol	Parameter	Conditions	Тур	Unit
R _{th(j-}	sp)	thermal resistance from junction to solder point		250	K/W



9. Characteristics

Table 9.Characteristics

 $T_j = 25 \ ^{\circ}C$ unless otherwise specified; measurements done on characterization boards.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)CBO}$	collector-base breakdown voltage	$I_{C} = 2.5 \ \mu A; \ I_{E} = 0 \ mA$	10	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	$I_{C} = 1 \text{ mA}; I_{B} = 0 \text{ mA}$	3.0	-	-	V
l _C	collector current		-	5	30	mA
I _{CBO}	collector-base cut-off current	$I_{E} = 0 \text{ mA}; V_{CB} = 4.5 \text{ V}$	-	-	100	nA
h _{FE}	DC current gain	$I_{C} = 2 \text{ mA}; V_{CE} = 2 \text{ V}$	205	380	555	
C _{CE}	collector-emitter capacitance	V _{CE} = 2 V; f = 1 MHz	-	145	-	fF
C _{EB}	emitter-base capacitance	V _{EB} = 0.5 V; f = 1 MHz	-	310	-	fF
C _{CB}	collector-base capacitance	$V_{CB} = 2 V$; f = 1 MHz	-	84	-	fF
f _T	transition frequency	$I_C = 25 \text{ mA}; V_{CE} = 3 \text{ V}; f = 2 \text{ GHz}; T_{amb} = 25 \text{ °C}$	-	53	-	GHz

NPN wideband silicon germanium RF transistor

Table 9. Characteristics ...continued

 $T_i = 25 \text{ °C}$ unless otherwise specified; measurements done on characterization boards.

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
G _{p(max)}	maximum power gain	$I_C = 5 \text{ mA}; V_{CE} = 3 \text{ V}; T_{amb} = 25 \text{ °C}$	[1]				
		f = 1.8 GHz		-	22.0	-	dB
		f = 6 GHz		-	15.0	-	dB
		I_C = 10 mA; V_{CE} = 3 V; T_{amb} = 25 °C	[1]				
		f = 1.8 GHz		-	23.6	-	dB
		f = 6 GHz		-	15.7	-	dB
		I_{C} = 25 mA; V_{CE} = 3 V; T_{amb} = 25 °C	[1]				
		f = 1.8 GHz		-	24.5	-	dB
		f = 6 GHz		-	15.8	-	dB
s ₂₁ ²	insertion power gain	$I_C = 5 \text{ mA}; V_{CE} = 3 \text{ V}; T_{amb} = 25 \text{ °C}$					
		f = 1.8 GHz		-	19.3	-	dB
		f = 6 GHz		-	11.1	-	dB
		I_C = 10 mA; V_{CE} = 3 V; T_{amb} = 25 °C					
		f = 1.8 GHz		-	21.3	-	dB
		f = 6 GHz		-	12.0	-	dB
		$I_C = 25 \text{ mA}; V_{CE} = 3 \text{ V}; T_{amb} = 25 \text{ °C}$					
		f = 1.8 GHz		-	22.3	-	dB
		f = 6 GHz		-	12.5	-	dB
NF _{min}	minimum noise figure	I_{C} = 5 mA; V_{CE} = 3 V; Γ_{S} = Γ_{opt} ; T_{amb} = 25 °C					
		f = 1.8 GHz		-	0.55	-	dB
		f = 6 GHz		-	0.75	-	dB
		I_C = 10 mA; V_{CE} = 3 V; Γ_S = Γ_{opt} ; T_{amb} = 25 °C					
		f = 1.8 GHz		-	0.7	-	dB
		f = 6 GHz		-	0.9	-	dB
		I_C = 25 mA; V_{CE} = 3 V; Γ_S = Γ_{opt} ; T_{amb} = 25 °C					
		f = 1.8 GHz		-	1.1	-	dB
		f = 6 GHz		-	1.2	-	dB
P _{L(1dB)}	output power at 1 dB gain compression	I_C = 5 mA; V_{CE} = 3 V; Z_S = Z_L = 50 Ω; T_{amb} = 25 °C					
		f = 1.8 GHz		-	-3.7	-	dBm
		f = 6 GHz		-	-1.6	-	dBm
		I _C = 10 mA; V _{CE} = 3 V; Z _S = Z _L = 50 Ω; T _{amb} = 25 °C					
		f = 1.8 GHz		-	3.5	-	dBm
		f = 6 GHz		-	5.4	-	dBm
		I _C = 25 mA; V _{CE} = 3 V; Z _S = Z _L = 50 Ω; T _{amb} = 25 °C					
		f = 1.8 GHz		-	11.7	-	dBm
		f = 6 GHz		_	12.7	-	dBm

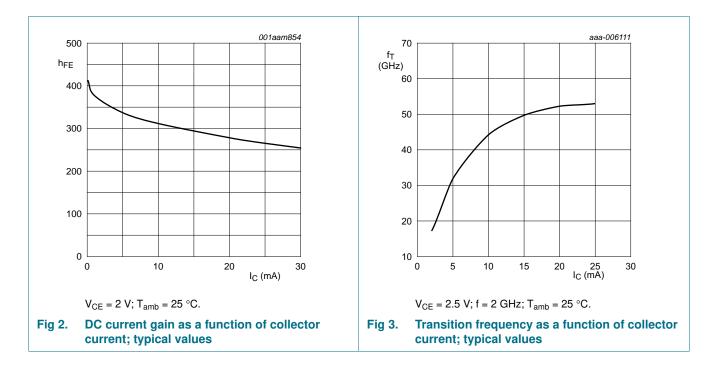
NPN wideband silicon germanium RF transistor

Table 9. Characteristics ...continued

 $T_i = 25 \text{ °C}$ unless otherwise specified; measurements done on characterization boards.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
IP3 ₀	output third-order intercept point	I_C = 5 mA; V _{CE} = 3 V; Z _S = Z _L = 50 Ω; T _{amb} = 25 °C				
		f = 1.8 GHz	-	14.7	-	dBm
		f = 6 GHz	-	19.0	-	dBm
		I_C = 10 mA; V _{CE} = 3 V; Z _S = Z _L = 50 Ω; T _{amb} = 25 °C				
		f = 1.8 GHz	-	23.8	-	dBm
		f = 6 GHz	-	25.3	-	dBm
		$\label{eq:IC} \begin{array}{l} I_{C} = 25 \text{ mA}; \ V_{CE} = 3 \ V; \ Z_{S} = Z_{L} = 50 \ \Omega; \\ T_{amb} = 25 \ ^{\circ}C \end{array}$				
		f = 1.8 GHz	-	25.5	-	dBm
		f = 6 GHz	-	26.9	-	dBm

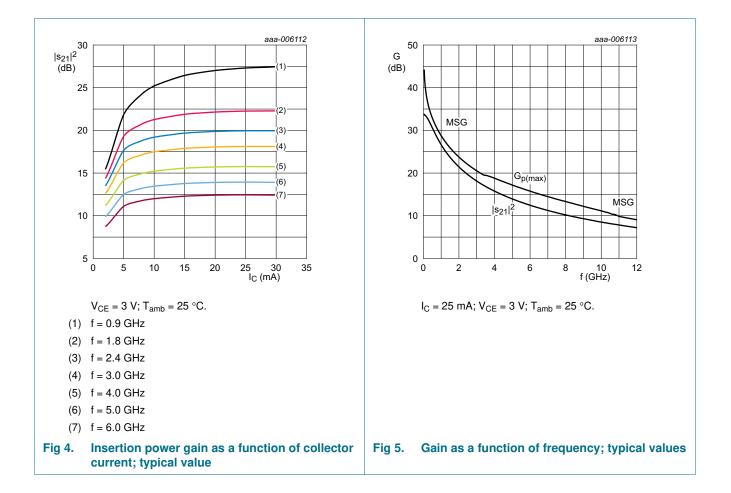
[1] $G_{p(max)}$ is the maximum power gain, if K > 1. If K < 1 then $G_{p(max)} = MSG$.



NXP Semiconductors

BFU730LX

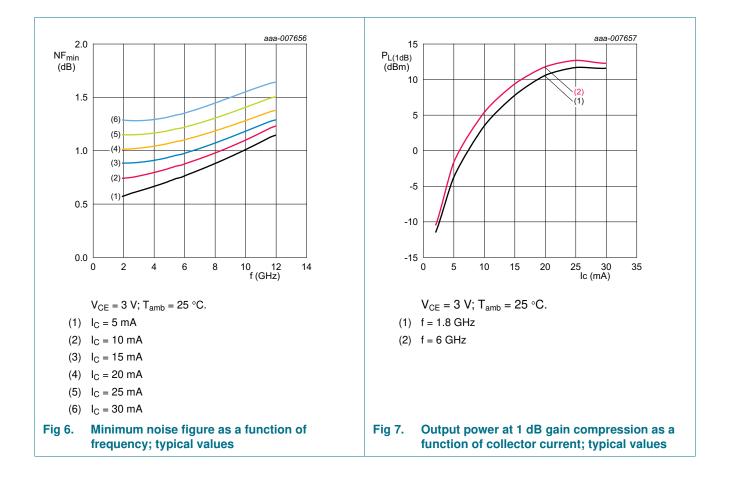
NPN wideband silicon germanium RF transistor



NXP Semiconductors

BFU730LX

NPN wideband silicon germanium RF transistor



NPN wideband silicon germanium RF transistor

10. Package outline

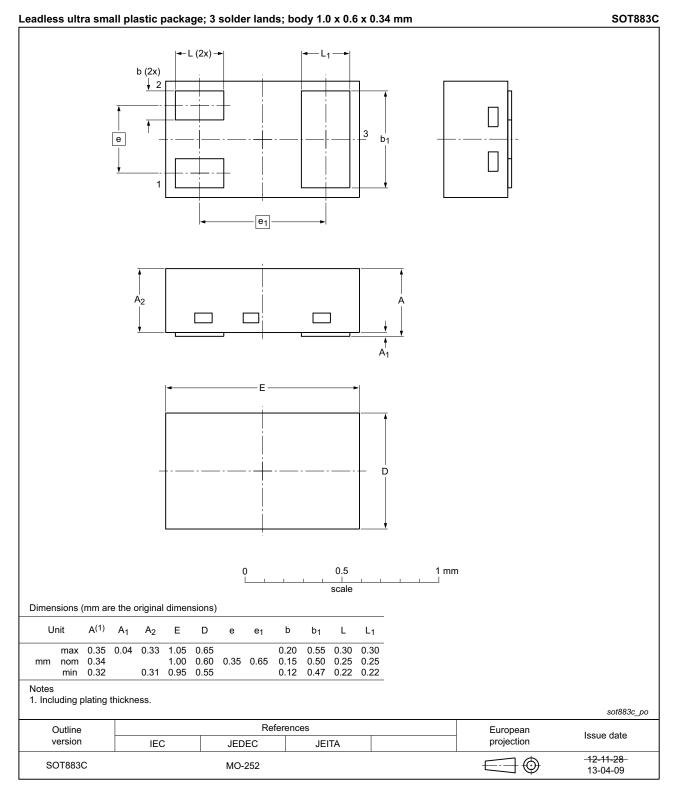


Fig 8. Package outline SOT883C

All information provided in this document is subject to legal disclaimers.

NPN wideband silicon germanium RF transistor

11. Abbreviations

Table 10.	Abbreviations
Acronym	Description
AMR	Automatic Meter Reading
DBS	Direct Broadcast Satellite
DRO	Dielectric Resonator Oscillator
GLONASS	GLObal NAvigation Satellite System
GPS	Global Positioning System
LNA	Low Noise Amplifier
LNB	Low Noise Block
NPN	Negative-Positive-Negative
RKE	Remote Keyless Entry
SDARS	Satellite Digital Audio Radio Service
SMD	Surface-Mounted Device
WiMAX	Worldwide Interoperability for Microwave Access
WLAN	Wireless Local Area Network

12. Revision history

Table 11. Revision hist	11. Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes	
BFU730LX v.1	20130508	Product data sheet	-	-	

NPN wideband silicon germanium RF transistor

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

13.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between NXP Semiconductors and its customer, unless NXP Semiconductors and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the NXP Semiconductors product is deemed to offer functions and qualities beyond those described in the Product data sheet.

13.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. NXP Semiconductors takes no responsibility for the content in this document if provided by an information source outside of NXP Semiconductors.

In no event shall NXP Semiconductors be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, NXP Semiconductors' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of NXP Semiconductors.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors and its suppliers accept no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using NXP Semiconductors products, and NXP Semiconductors accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the NXP Semiconductors products product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

NXP Semiconductors does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using NXP Semiconductors products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). NXP does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. NXP Semiconductors hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of NXP Semiconductors products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

© NXP B.V. 2013. All rights reserved.

NPN wideband silicon germanium RF transistor

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

Non-automotive qualified products — Unless this data sheet expressly states that this specific NXP Semiconductors product is automotive qualified, the product is not suitable for automotive use. It is neither qualified nor tested in accordance with automotive testing or application requirements. NXP Semiconductors accepts no liability for inclusion and/or use of non-automotive qualified products in automotive equipment or applications.

In the event that customer uses the product for design-in and use in automotive applications to automotive specifications and standards, customer (a) shall use the product without NXP Semiconductors' warranty of the product for such automotive applications, use and specifications, and (b) whenever customer uses the product for automotive applications beyond NXP Semiconductors' specifications such use shall be solely at customer's own risk, and (c) customer fully indemnifies NXP Semiconductors for any liability, damages or failed product claims resulting from customer design and use of the product for automotive applications beyond NXP Semiconductors' standard warranty and NXP Semiconductors' product specifications.

Translations — A non-English (translated) version of a document is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

13.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

14. Contact information

For more information, please visit: <u>http://www.nxp.com</u>

For sales office addresses, please send an email to: salesaddresses@nxp.com

NPN wideband silicon germanium RF transistor

15. Contents

1	Product profile 1
1.1	General description 1
1.2	Features and benefits 1
1.3	Applications 1
1.4	Quick reference data 2
2	Pinning information 2
3	Ordering information 2
4	Marking
5	Design support 3
6	Limiting values
7	Recommended operating conditions 4
8	Thermal characteristics 4
9	Characteristics 4
10	Package outline 9
11	Abbreviations 10
12	Revision history 10
13	Legal information 11
13.1	Data sheet status 11
13.2	Definitions 11
13.3	Disclaimers 11
13.4	Trademarks 12
14	Contact information 12
15	Contents 13

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

© NXP B.V. 2013.

All rights reserved.

For more information, please visit: http://www.nxp.com For sales office addresses, please send an email to: salesaddresses@nxp.com

Date of release: 8 May 2013 Document identifier: BFU730LX